

Features

- 600 V, 30 A, Low Collector-Emitter Saturation Voltage ($V_{CE(sat)}$)
- Trench-Gate Field-Stop technology
- Optimized for conduction
- RoHS compliant*

Applications

- Switch-Mode Power Supplies (SMPS)
- Uninterruptible Power Sources (UPS)
- Power Factor Correction (PFC)
- Induction heating

BIDW30N60T Insulated Gate Bipolar Transistor (IGBT)

General Information

The Bourns® Model BIDW30N60T IGBT device combines technology from a MOS gate and a bipolar transistor for an optimum component for high voltage and high current applications. This device uses Trench-Gate Field-Stop technology providing greater control of dynamic characteristics with a lower Collector-Emitter Saturation Voltage ($V_{CE(sat)}$) and fewer switching losses. In addition, this structure gives a lower thermal resistance $R_{(th)}$.

Additional Information

Click these links for more information:



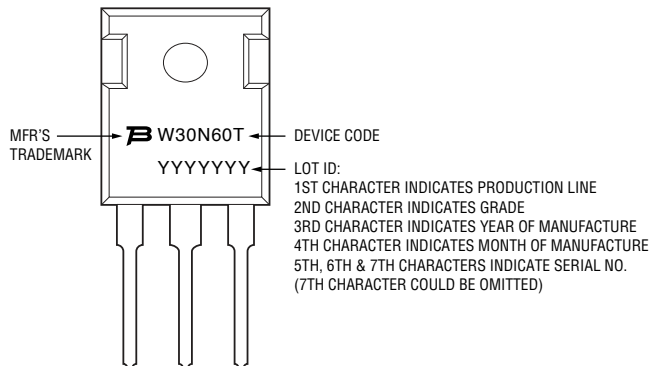
Maximum Electrical Ratings ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|---|-------------|-------------|------------------|
| Collector-Emitter Voltage | V_{CES} | 600 | V |
| Continuous Collector Current ($T_C = 25\text{ }^\circ\text{C}$), limited by T_{jmax} | I_C | 60 | A |
| Continuous Collector Current ($T_C = 100\text{ }^\circ\text{C}$), limited by T_{jmax} | I_C | 30 | A |
| Pulsed Collector Current, t_p limited by T_{jmax} | I_{CP} | 90 | A |
| Gate-Emitter Voltage | V_{GE} | ± 20 | V |
| Continuous Forward Current ($T_C = 25\text{ }^\circ\text{C}$), limited by T_{jmax} | I_F | 60 | A |
| Continuous Forward Current ($T_C = 100\text{ }^\circ\text{C}$), limited by T_{jmax} | I_F | 30 | A |
| Short-circuit Withstand Time ($V_{CE} = 300\text{ V}$, $V_{GE} = 15\text{ V}$) | T_{SC} | 10 | μs |
| Total Power Dissipation | P_{total} | 230 | W |
| Storage Temperature | T_{STG} | -55 to +150 | $^\circ\text{C}$ |
| Operating Junction Temperature | T_j | -55 to +150 | $^\circ\text{C}$ |

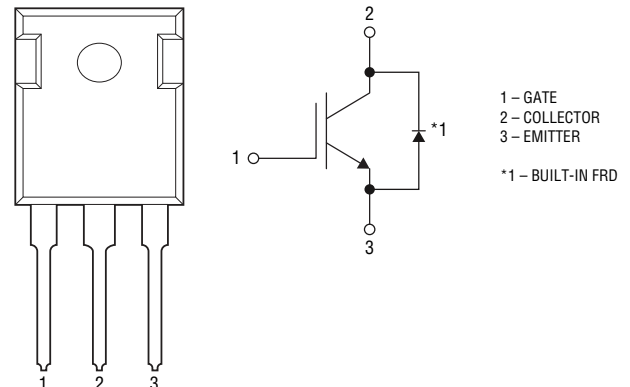
Thermal Resistance

| Parameter | Symbol | Max | Unit |
|--|-----------------------|------|--------------------|
| IGBT Thermal Resistance Junction - Case | $R_{th(j-c)}_{IGBT}$ | 0.54 | $^\circ\text{C/W}$ |
| Diode Thermal Resistance Junction - Case | $R_{th(j-c)}_{Diode}$ | 1.2 | $^\circ\text{C/W}$ |

Typical Part Marking



Internal Circuit



*RoHS Directive 2015/863, Mar 31, 2015 and Annex.
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BIDW30N60T Insulated Gate Bipolar Transistor (IGBT)

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Static Electrical Characteristics ($T_C = 25\text{ }^\circ\text{C}$, Unless Otherwise Specified)

| Parameter | Symbol | Conditions | Value | | | Unit |
|--------------------------------------|---------------|--|-------|------|-----------|---------------|
| | | | Min. | Typ. | Max. | |
| Collector-Emitter Breakdown Voltage | BV_{CES} | $V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$ | 600 | — | — | V |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $V_{GE} = 15\text{ V}, I_C = 30\text{ A}$ $T_C = 25\text{ }^\circ\text{C}$ | — | 1.65 | — | V |
| | | $V_{GE} = 15\text{ V}, I_C = 30\text{ A}$ $T_C = 125\text{ }^\circ\text{C}$ | — | 1.9 | — | |
| Diode Forward On-Voltage | V_F | $I_F = 30\text{ A}, T_C = 25\text{ }^\circ\text{C}$ | — | 1.8 | — | V |
| | | $I_F = 30\text{ A}, T_C = 125\text{ }^\circ\text{C}$ | — | 1.5 | — | V |
| Gate Threshold Voltage | $V_{GE(th)}$ | $V_{CE} = V_{GE}, I_C = 250\text{ }\mu\text{A}$ | 4.0 | 5.0 | 6.5 | V |
| Collector Cut-off Current | I_{CES} | $V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$ | — | — | 200 | μA |
| Gate-Emitter Leakage Current | I_{GES} | $V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$ | — | — | ± 400 | nA |

Dynamic Electrical Characteristics ($T_C = 25\text{ }^\circ\text{C}$, Unless Otherwise Specified)

| Parameter | Symbol | Conditions | Value | | | Unit |
|------------------------------|-----------|--|-------|------|------|------|
| | | | Min. | Typ. | Max. | |
| Input Capacitance | C_{ies} | $V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V},$ $f = 1\text{ MHz}$ | — | 1650 | — | pF |
| Output Capacitance | C_{oes} | | — | 130 | — | |
| Reverse Transfer Capacitance | C_{res} | | — | 35 | — | |
| Total Gate Charge | Q_g | $V_{CE} = 400\text{ V}, V_{GE} = 15\text{ V}$ $I_C = 30.0\text{ A}$ | — | 76 | — | nC |
| Gate-Emitter Charge | Q_{ge} | | — | 20 | — | |
| Gate-Collector Charge | Q_{gc} | | — | 38 | — | |

IGBT Switching Characteristics (Inductive Load, $T_C = 25\text{ }^\circ\text{C}$, unless otherwise specified)

| Parameter | Symbol | Conditions | Value | | | Unit |
|---------------------------|--------------|--|-------|------|------|------|
| | | | Min. | Typ. | Max. | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{CE} = 400\text{ V}, V_{GE} = 15\text{ V}$ $I_C = 30.0\text{ A}, R_G = 10\text{ }\Omega$ | — | 30 | — | ns |
| Current Rise Time | t_r | | — | 105 | — | ns |
| Turn-off Delay Time | $t_{d(off)}$ | | — | 67 | — | ns |
| Current Fall Time | t_f | | — | 100 | — | ns |
| Turn-on Switching Energy | E_{on} | | — | 1.85 | — | mJ |
| Turn-off Switching Energy | E_{off} | | — | 0.45 | — | mJ |
| Total Switching Energy | E_{ts} | | — | 2.3 | — | mJ |

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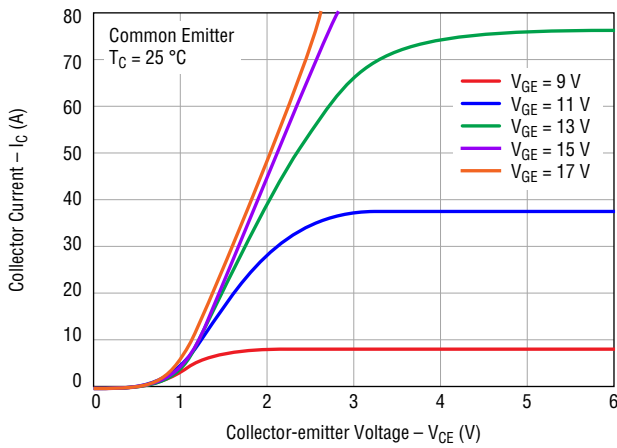
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Diode Switching Characteristics ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise specified)

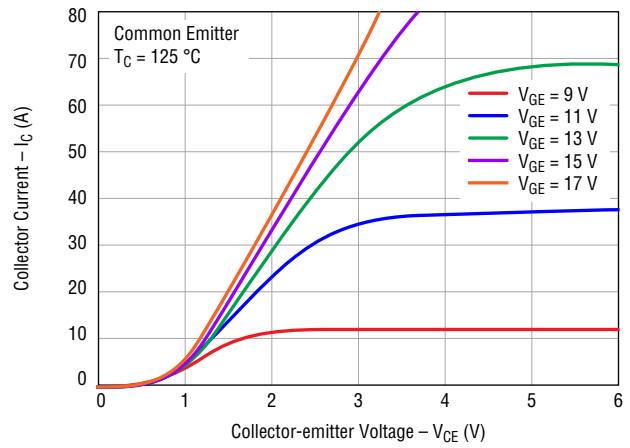
| Parameter | Symbol | Conditions | Value | | | Unit |
|-------------------------|----------|---|-------|------|------|------|
| | | | Min. | Typ. | Max. | |
| Reverse Recovery Time | t_{rr} | $di_F/dt = 200\text{ A}/\mu\text{s}$ $I_F = 30.0\text{ A}$ | — | 40 | — | ns |
| Reverse Recovery Charge | Q_{rr} | | — | 90 | — | nC |

Electrical Characteristic Performance

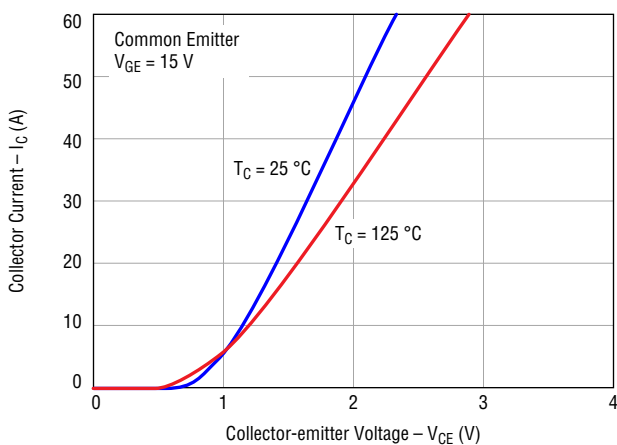
Typical Output Characteristics



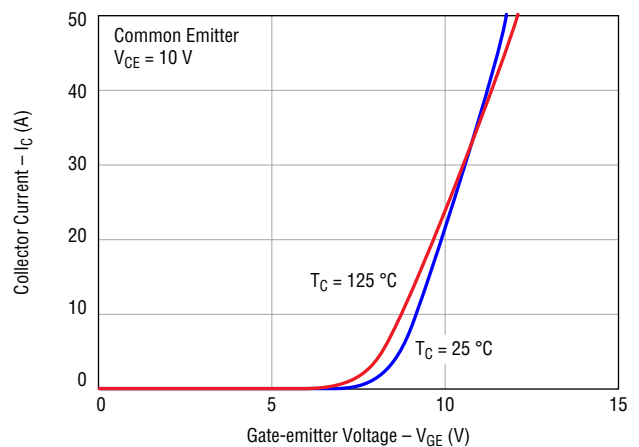
Typical Output Characteristics



Typical Saturation Voltage Characteristics



Typical Transfer Characteristics



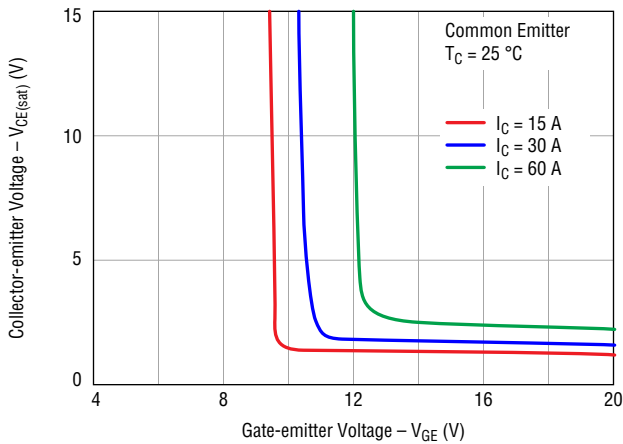
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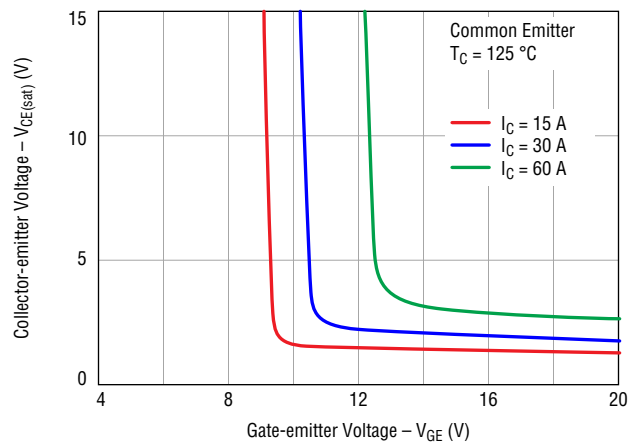
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Electrical Characteristic Performance (continued)

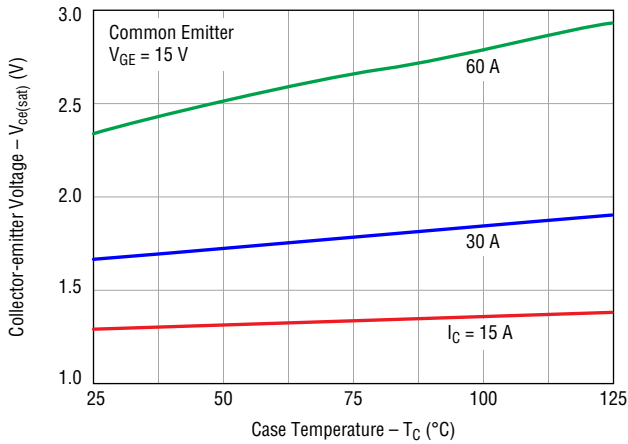
Typical $V_{CE(sat)}$ vs V_{GE} @ $T_C = 25^\circ\text{C}$



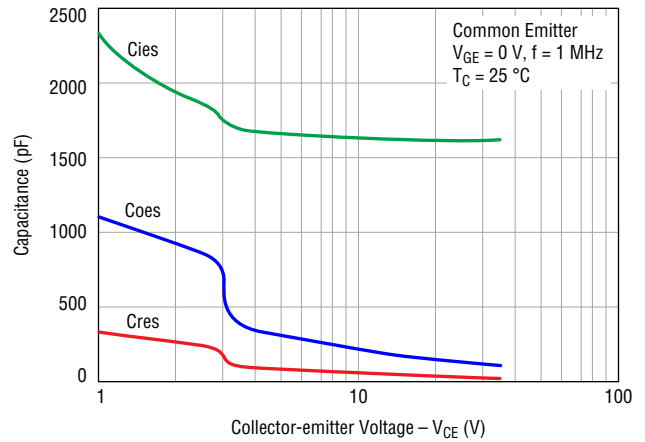
Typical $V_{CE(sat)}$ vs V_{GE} @ $T_C = 125^\circ\text{C}$



Typical $V_{CE(sat)}$ vs Case Temperature



Typical Capacitance Characteristics



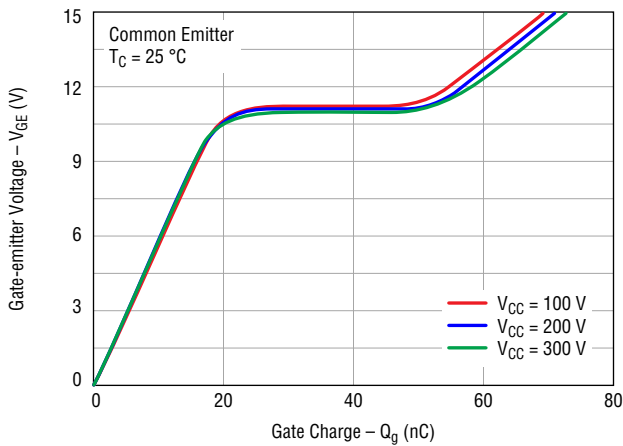
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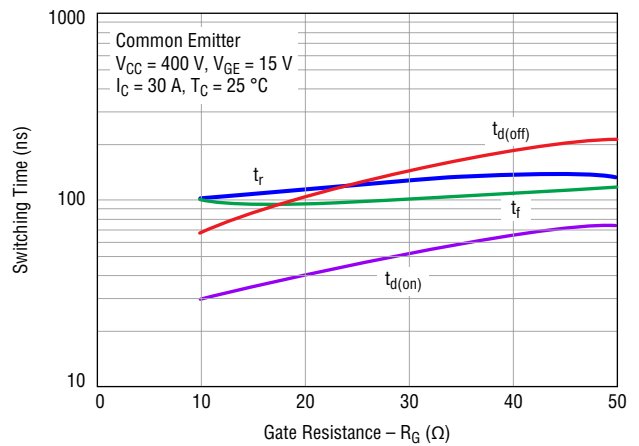
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Electrical Characteristic Performance (continued)

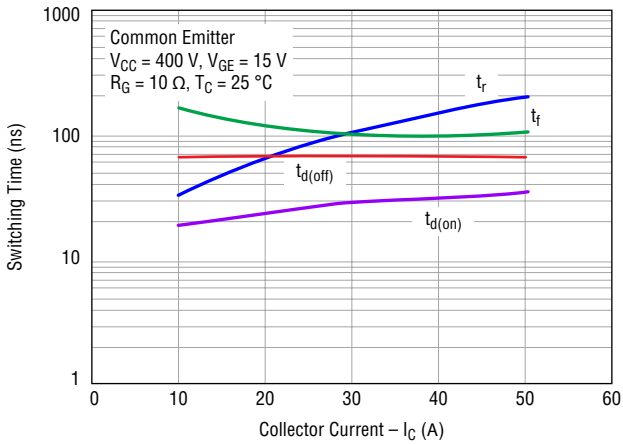
Typical Gate Charge Characteristics



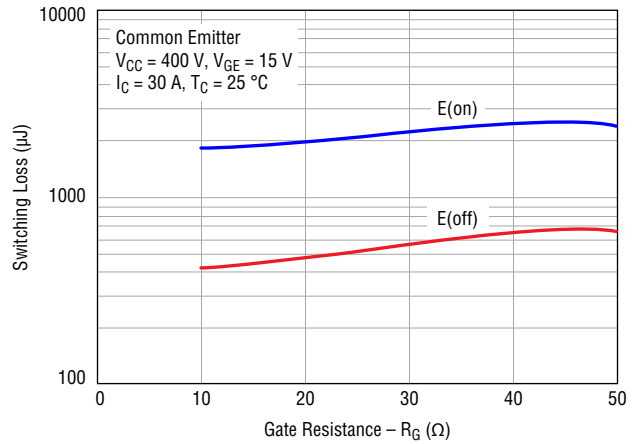
Typical Switching Time Characteristics vs R_G



Typical Switching Time Characteristics vs I_C



Typical Switching Loss vs R_G

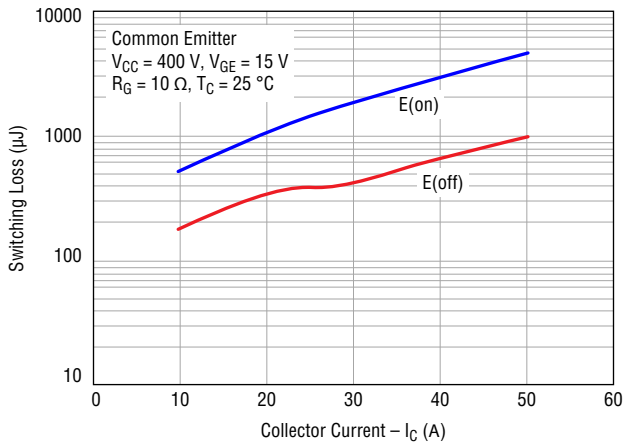


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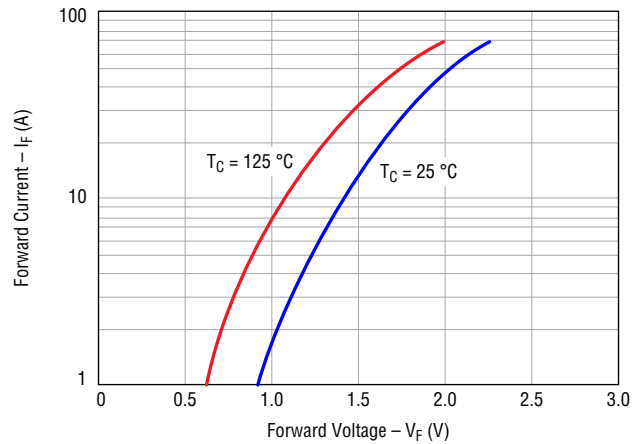


Electrical Characteristic Performance (continued)

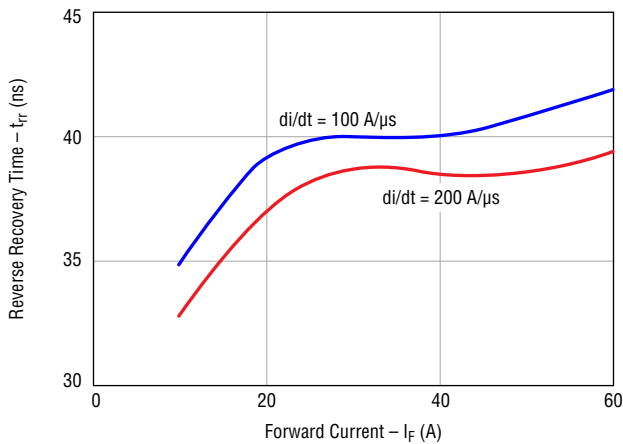
Typical Switching Loss Characteristics vs I_C



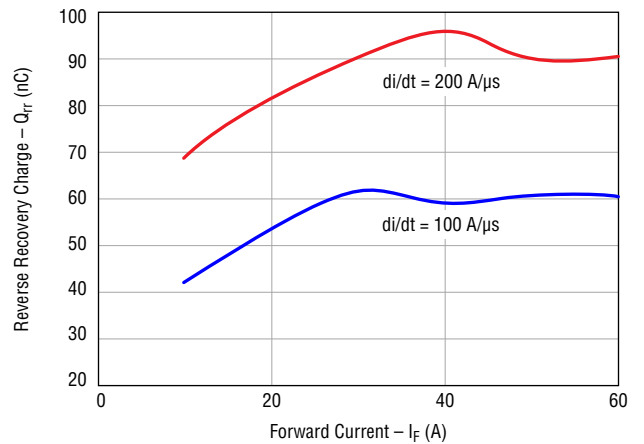
Typical Diode I_F vs V_F



Typical Reverse Recovery Time vs I_F



Typical Reverse Recovery Charge vs I_F



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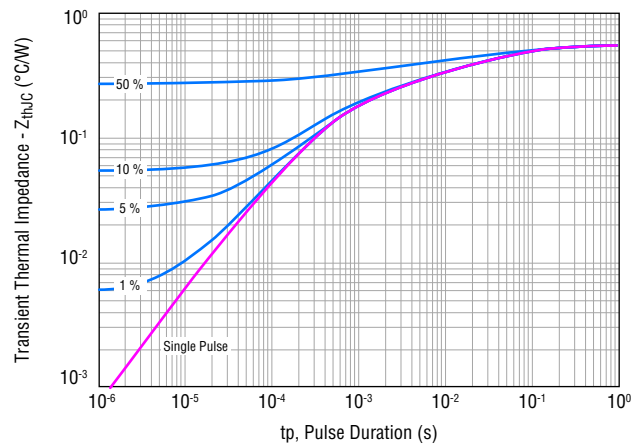
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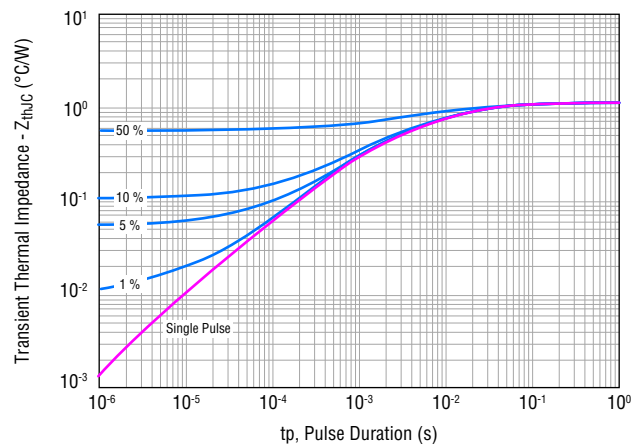


Electrical Characteristic Performance (continued)

IGBT Transient Thermal Impedance vs $t_{p(on)}$ Duration ($D=t_p/T$)



Diode Transient Thermal Impedance vs $t_{p(on)}$ Duration ($D=t_p/T$)



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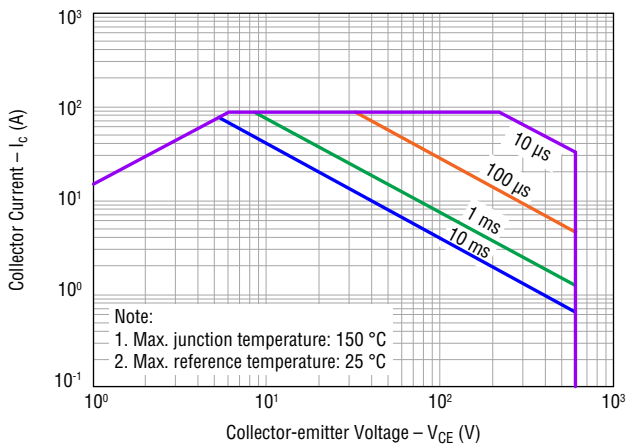
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Electrical Characteristic Performance (continued)

Forward Bias Safe Operating Area

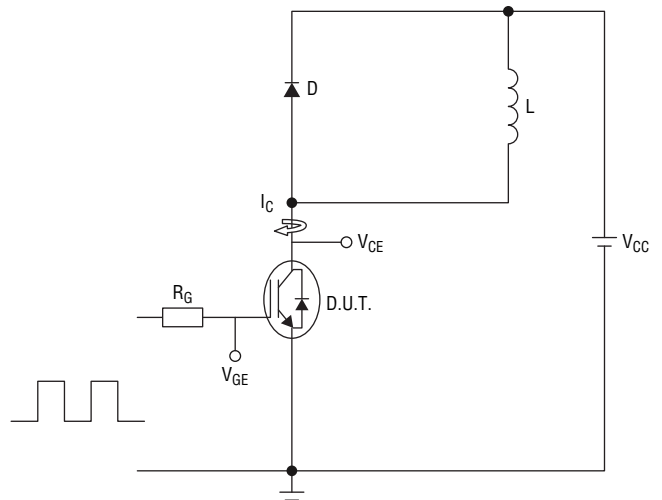


How to Order

B I D W 30 N 60 T

- B = Bourns®
- I = IGBT
- Type
D = Discrete
- Package Code
W = TO-247
- Current Rating
30 = 30 A
- Device Type
N = N-channel
- Nominal Voltage (divided by 10)
60 = 600 V
- Optimization
T = Medium Speed

Inductive Load Test Circuit



$L = 1.87 \text{ mH}$, $V_{CE} = 400 \text{ V}$, $V_{GE} = 15 \text{ V}$, $I_C = 30 \text{ A}$, $R_G = 10 \Omega$

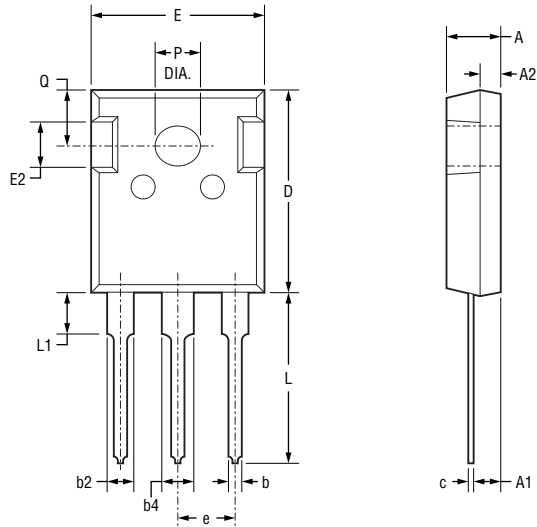
Environmental Characteristics

ESD Class (HBM) 2

BIDW30N60T Insulated Gate Bipolar Transistor (IGBT)



Product Dimensions



DIMENSIONS: $\frac{\text{MM}}{\text{(INCHES)}}$

| Symbol | Min. | Nom. | Max. |
|--------|---------------------------|------------------------|------------------------|
| A | $\frac{4.80}{(.189)}$ | $\frac{5.00}{(.197)}$ | $\frac{5.20}{(.205)}$ |
| A1 | $\frac{2.21}{(.087)}$ | $\frac{2.41}{(.095)}$ | $\frac{2.59}{(.102)}$ |
| A2 | $\frac{1.85}{(.073)}$ | $\frac{2.00}{(.079)}$ | $\frac{2.15}{(.085)}$ |
| b | $\frac{1.11}{(.044)}$ | — | $\frac{1.36}{(.054)}$ |
| b2 | $\frac{1.91}{(.075)}$ | — | $\frac{2.25}{(.089)}$ |
| b4 | $\frac{2.91}{(.115)}$ | — | $\frac{3.25}{(.128)}$ |
| c | $\frac{0.51}{(.020)}$ | — | $\frac{0.75}{(.030)}$ |
| D | $\frac{20.80}{(.819)}$ | $\frac{21.00}{(.827)}$ | $\frac{21.30}{(.839)}$ |
| E | $\frac{15.50}{(.610)}$ | $\frac{15.80}{(.622)}$ | $\frac{16.10}{(.634)}$ |
| E2 | $\frac{4.40}{(.173)}$ | $\frac{5.00}{(.197)}$ | $\frac{5.20}{(.205)}$ |
| e | $\frac{5.44}{(.214)}$ BSC | | |
| L | $\frac{19.72}{(.776)}$ | $\frac{19.92}{(.784)}$ | $\frac{20.22}{(.796)}$ |
| L1 | — | — | $\frac{4.30}{(.169)}$ |
| P | $\frac{3.40}{(.134)}$ | — | $\frac{3.80}{(.150)}$ |
| Q | $\frac{5.60}{(.220)}$ | $\frac{5.80}{(.228)}$ | $\frac{6.00}{(.236)}$ |

Packaging Specifications

BIDW30N60T 30 pieces per tube



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[IGW40N120H3FKSA1](#) [VS-CPV364M4KPBF](#) [NGTB25N120FL2WAG](#) [NGTG40N120FL2WG](#) [RJH60F3DPQ-A0#T0](#)
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